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(54) **SIGE BASED GATE DRIVEN PMOS TRIGGER CIRCUIT**

(75) Inventors: **Wen-Han Wang**, Hsinchu (TW); **Kuo-Ji Chen**, Taipei County (TW)

(73) Assignee: **Taiwan Semiconductor Manufacturing Co., Ltd.**, Hsin-Chu (TW)

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(58) **Field of Classification Search**
USPC 361/56
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Primary Examiner — Rexford Barnie

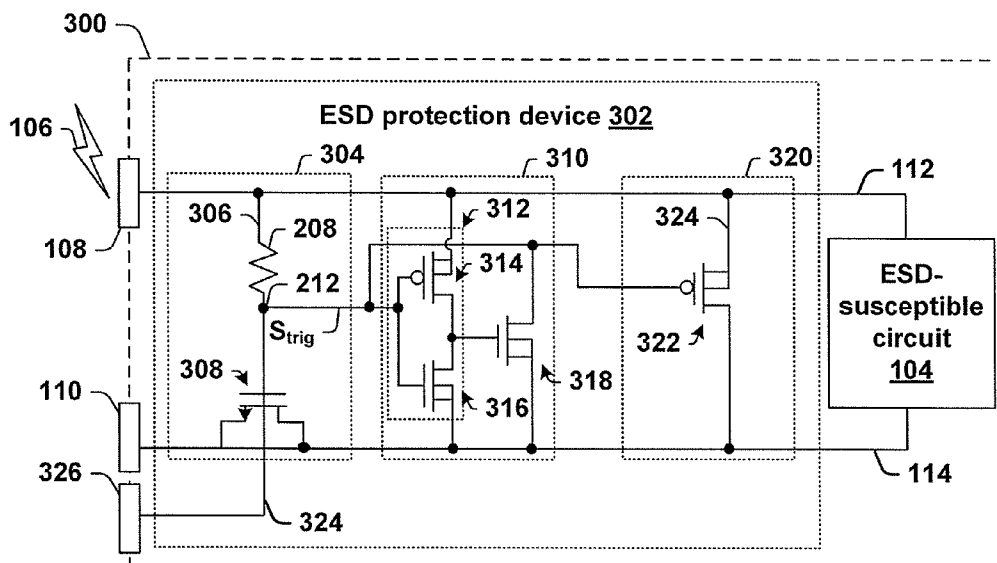
Assistant Examiner — Angela Brooks

(74) *Attorney, Agent, or Firm* — Eschweiler & Associates, LLC

(57) **ABSTRACT**

Some embodiments of the present disclosure relate to a low-power, area efficient ESD protection device that provides ESD protection to an ESD susceptible circuit. The ESD protection device has a trigger circuit with a resistor. The resistor has a first terminal connected to the first external pin and a second terminal connected directly to a gate of a SiGe based PMOS shunt transistor. The trigger circuit generates a trigger signal that drives the gate of the PMOS device to shunt power away from the ESD susceptible circuit when an ESD event is present. The SiGe based PMOS shunt transistor has a lower gate leakage than a conventional NMOS shunt transistors, thereby providing for an ESD circuit with a low leakage current at small gate lengths.

21 Claims, 5 Drawing Sheets



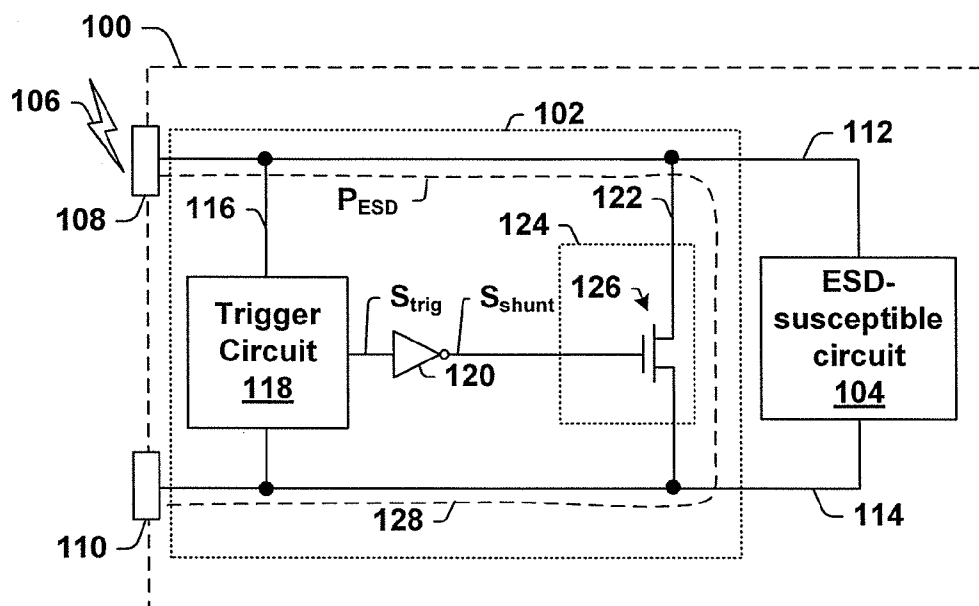


Fig. 1

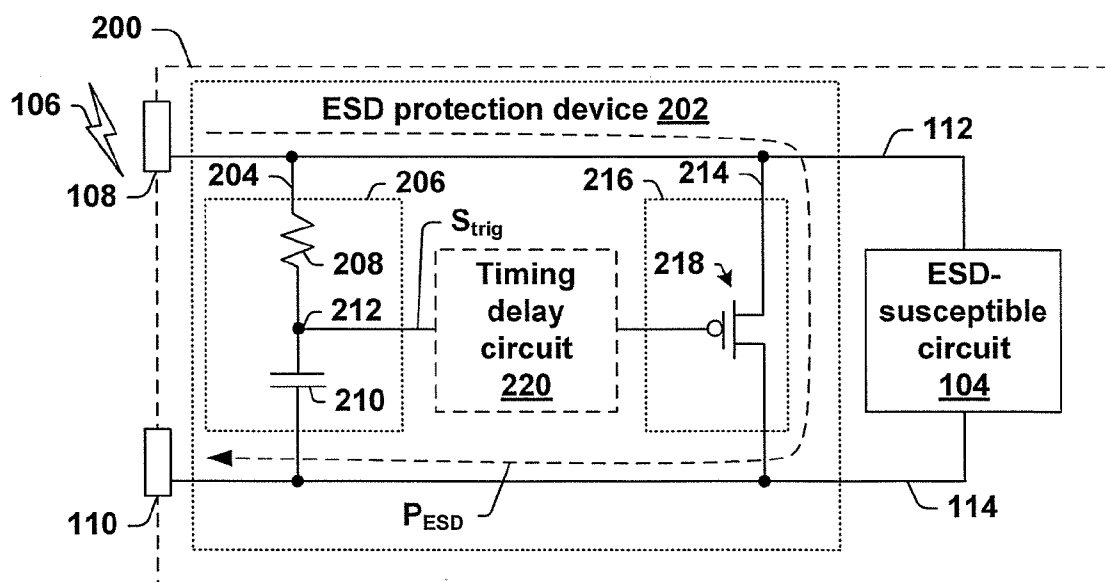
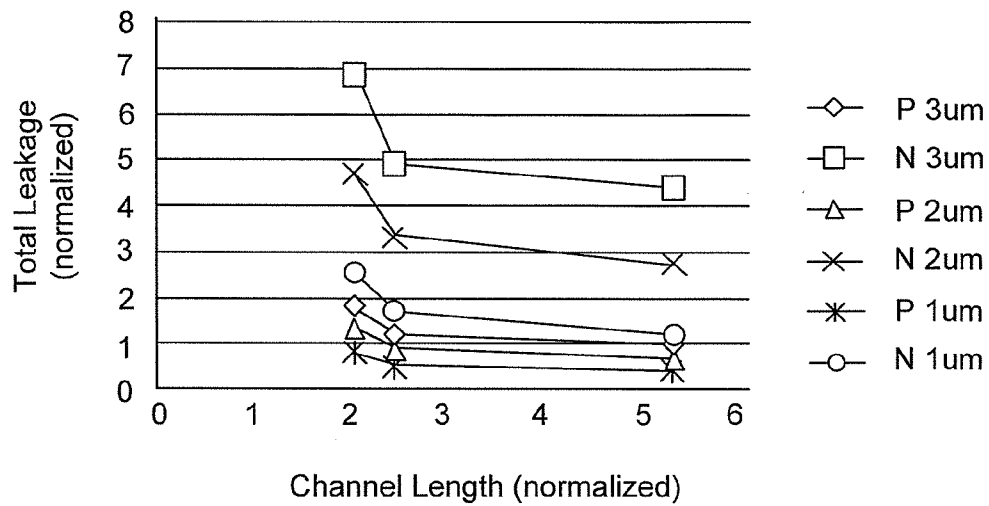
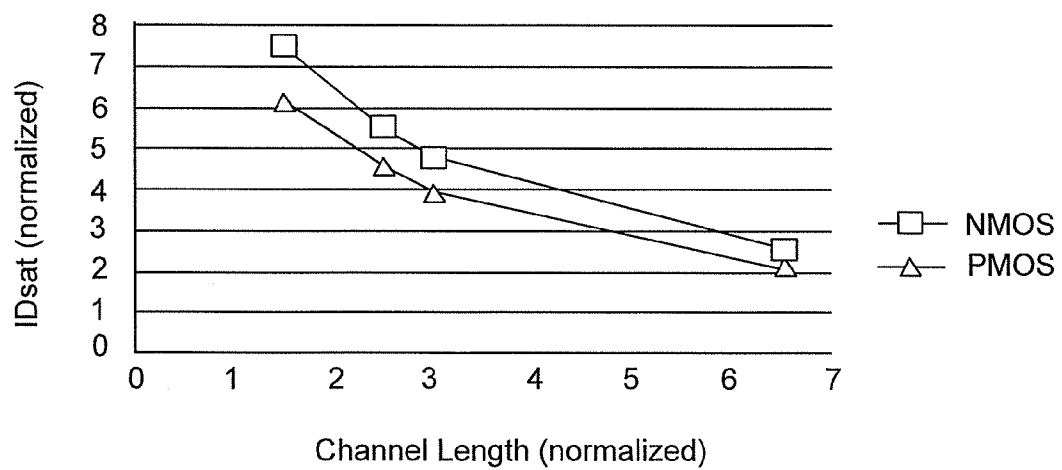


Fig. 2A

222 ↗

**Fig. 2B**

224 ↗

**Fig. 2C**

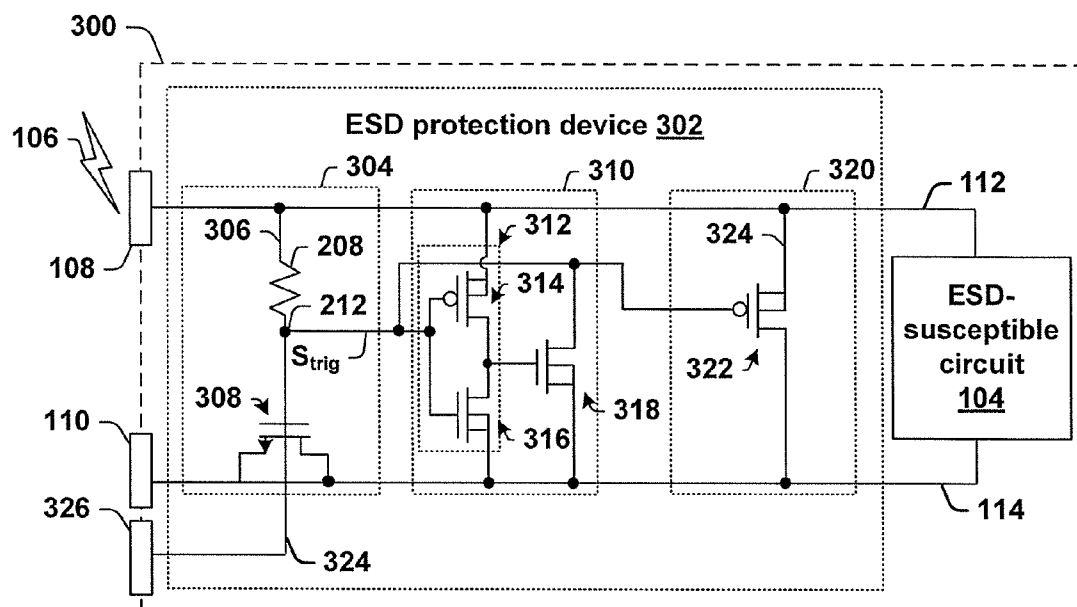


Fig. 3

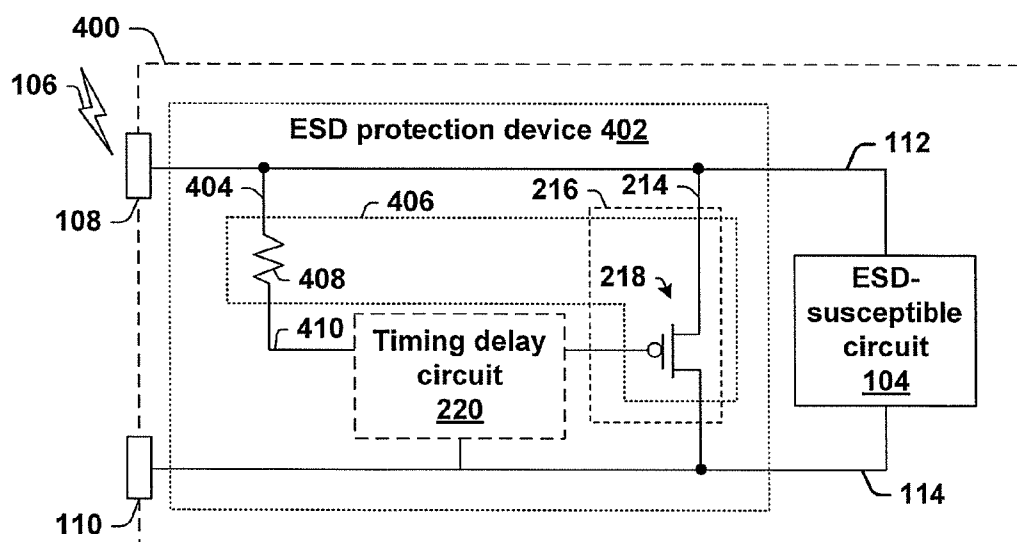
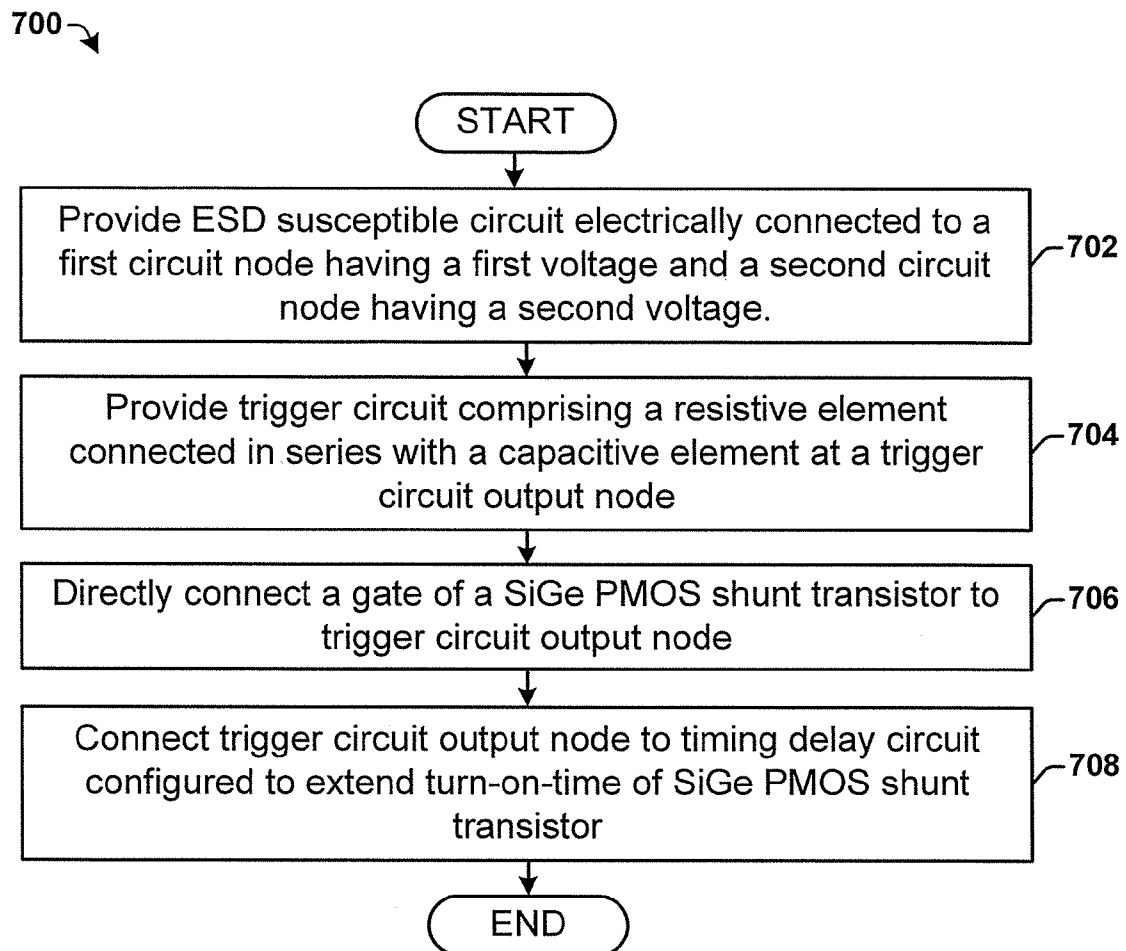


Fig. 4

Fig. 6

**Fig. 7**

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SIG E BASED GATE DRIVEN PMOS TRIGGER CIRCUIT

BACKGROUND

An electrostatic discharge (ESD) event is a sudden and unexpected voltage and/or current discharge that transfers energy to an electronic device from an outside body (e.g., a human body, which can be approximated in modeling by a human body model (HBM)). ESD events can damage electronic devices, for example by “blowing out” a gate oxide of a transistor in cases of high voltage or by “melting” an active region area of a device in cases of high current, causing junction failure. If devices are damaged by an ESD event, the electronic product can be rendered less operable than desired, or can even be rendered inoperable altogether.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 shows an integrated circuit that makes use of a conventional ESD protection device.

FIG. 2A shows a block diagram of some embodiments of an integrated circuit having an ESD protection device comprising a SiGe PMOS shunt transistor.

FIG. 2B illustrates a graph showing the leakage current of both NMOS and PMOS shunt transistors as a function of channel length.

FIG. 2C illustrates a graph showing the saturation drain current ($I_{D,sat}$) of both NMOS and PMOS shunt transistors as a function of channel length.

FIG. 3 shows a circuit schematic of some embodiments of a disclosed ESD protection device having a SiGe PMOS shunt transistor.

FIG. 4 shows a block diagram of some alternative embodiments of an integrated circuit having an ESD protection device comprising a SiGe PMOS shunt transistor.

FIG. 5 shows a circuit schematic of some alternative embodiments of a disclosed ESD protection device having a SiGe PMOS shunt transistor.

FIG. 6 shows some embodiments of a cross-sectional view of a substrate comprising a silicon germanium (SiGe) PMOS shunt transistor and a resistive element.

FIG. 7 shows a flow diagram of some embodiments of a method of forming an ESD protection device comprising a SiGe PMOS shunt transistor.

DETAILED DESCRIPTION

One or more implementations of the present disclosure will now be described with reference to the attached drawings, wherein like reference numerals are used to refer to like elements throughout. The drawings are not necessarily drawn to scale.

To protect electronic devices from ESD events, engineers have developed ESD protection devices. FIG. 1 shows a block diagram of an integrated circuit **100** comprising a conventional ESD protection device **102** configured to mitigate damage to an ESD susceptible circuit **104** due to an ESD event **106**. The ESD susceptible circuit **104**, having one or more semiconductor devices, is electrically connected to an exterior circuit assembly (not shown) via one or more external IC pins, **108** and **110**, respectively held at a first voltage (e.g., V_{DD}) and a second voltage (e.g., GND). The external IC pins **108,110** can be supply pins that supply a DC supply voltage (e.g., V_{DD} or V_{SS}) to the circuit **104**, or can be input/output (I/O) pins that transfer input or output signals there from, for example.

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The ESD protection device **102** is electrically connected in parallel with the ESD susceptible circuit **104** and the external IC pins **108,110** and includes a first electrical path **116** extending between first and second circuit nodes, **112** and **114**. The first electrical path **116** comprises a trigger circuit **118** configured to generate a trigger signal S_{trig} depending on whether an ESD event **106** is present. The trigger signal S_{trig} is provided to an inverter **120**, which inverts the trigger signal S_{trig} to generate a shunt control signal S_{shunt} that is output to a voltage controlled shunt network **124** comprising an NMOS shunt transistor **126**. The NMOS shunt transistor **126** is electrically connected to a second electrical path **122**, extending in parallel with the first electrical path **116** between the first and second circuit nodes, **112** and **114**.

In a power-on situation, and in the absence of an ESD event **106**, the trigger signal S_{trig} has a relatively high voltage, which is inverted to a relatively low voltage (e.g., representing a logical “0” state) that is provided to the gate of NMOS shunt transistor **126**, thereby turning off the NMOS shunt transistor **126** and preventing leakage between the first and second circuit nodes, **112** and **114**, during normal operation. When an impinging ESD event **106** is present, the trigger signal S_{trig} obtains a relatively low voltage, which is inverted to a relatively high voltage (e.g., representing logical “1” state) that is provided to the gate of NMOS shunt transistor **126**, thereby turning on the NMOS shunt transistor **126** and causing energy to be diverted away from the ESD-susceptible circuit **104** via the second electrical path **122** (i.e., along path P_{ESD}) for the duration of the ESD event **106**.

Conventional ESD protection devices have used NMOS shunt transistors because they provide for good performance (e.g., a fast turn-on time, high mobility of electrons, and high saturation drive current). However, it has been appreciated that as transistor devices decrease in size the channel length of the NMOS shunt transistor **126** decreases, causing the leakage current (e.g., from junctions and/or from gate oxides) to increase. Increases in leakage current increase power consumption of the circuit, thereby inducing shorter battery life in handheld electronic devices. Accordingly, in emerging technology nodes (e.g., 32 nm, 22 nm, etc.), designers have to design NMOS shunt transistors having larger channel lengths to compensate for increased leakage current. However, using devices with larger channel lengths within an integrated circuit increases the cost of an integrated circuit in terms of area.

Accordingly, the present disclosure relates to an area efficient ESD circuit configured to provide for a low leakage current. In some embodiments, the disclosed ESD circuit comprises an ESD protection device disposed between an ESD susceptible circuit and first and second external pins. The ESD protection device comprises a trigger circuit having a resistive element. The resistive element comprises a first terminal connected to a first circuit node associated with the first external pin and a second terminal connected directly to a gate of a silicon germanium (SiGe) PMOS shunt transistor. The trigger circuit is configured to generate a trigger signal that drives the gate of the SiGe PMOS shunt transistor in manner that causes the SiGe PMOS shunt transistor to shunt power away from the ESD susceptible circuit when an ESD event is present. The SiGe PMOS shunt transistor comprises a lower gate leakage than a conventional NMOS shunt transistors, thereby providing the disclosed ESD circuit with a low leakage current at small gate lengths (i.e., small integrated chip area).

FIG. 2A shows some embodiments of an integrated circuit **200** having a disclosed ESD protection device **202** configured to protect an ESD susceptible circuit **104** having one or more semiconductor devices from an ESD event **106**.

The ESD protection device **202** is arranged between external pins, **108** and **110**, and the ESD susceptible circuit **104**. In some embodiments, the ESD susceptible circuit **104** can be electrically connected to first and second circuit nodes, **112** and **114**, which can be associated with first and second external IC pins, **108** and **110**, respectively. The first circuit node **112** is held at the first voltage (e.g., V_{DD}) and the second circuit node **114** is held at a second voltage (e.g., V_{SS} , GND). It will be appreciated that although FIG. 2A shows the first and second circuit nodes **112**, **114** electrically connected to external IC pins **108**, **110**, in other embodiments the first and second circuit nodes **112**, **114** can be located on internal nodes within the integrated circuit **200**.

The ESD protection device **202** includes a first electrical path **204** extending between the first and second circuit nodes **112**, **114**. The first electrical path **204** includes a trigger circuit **206** configured to generate a trigger signal S_{trig} having a value that depends on whether an ESD event **106** is present. For example, if an ESD event **106** is not present the trigger signal has a value equal to a logical “1”. However, if an ESD event **106** is present, the trigger signal will drop to a value equal to a logical “0” for a duration defined by an RC time constant of the trigger circuit.

In some embodiments, the trigger circuit **206** comprises a resistive element **208** (e.g., a polysilicon resistor) connected in series with a capacitive element **210** (e.g., a MOS capacitor). The resistive element **208** has a first terminal connected to the first circuit node **112** (e.g., 3.3 V) and a second terminal connected to a trigger circuit output node **212**. The capacitive element **210** has a first terminal connected to the trigger circuit output node **212** and a second terminal connected to the second circuit node **114** (e.g., V_{SS} , GND).

A second electrical path **214** that extends between the first and second circuit nodes, **112** and **114**, comprises a voltage controlled shunt network **216**. The second electrical path **214** is in parallel with the first electrical path **204**. The voltage-controlled shunt network **216** comprises a PMOS shunt transistor **218** adapted to selectively shunt energy from the ESD event **106** over the second electrical path **214** based on the trigger signal S_{trig} . A gate of the PMOS shunt transistor **218** is directly connected to the trigger circuit output node **212** (i.e., directly connected to the second terminal of the resistive element **208**), so that the gate receives a voltage value that is substantially equal to the voltage value at the trigger circuit output node **212** (i.e., that corresponds to a same logical state as the voltage value at trigger circuit output node **212**).

In some embodiments, the PMOS shunt transistor **218** comprises a SiGe PMOS transistor. It has been appreciated that in a SiGe process, the PMOS shunt transistor **218** is formed with a gate oxide that has a naturally lower leakage current than a comparable NMOS shunt transistor (e.g., NMOS shunt transistor **126**). For example, FIG. 2B illustrates a graph **222** showing the leakage current of both NMOS and PMOS shunt transistors (y-axis) as a function of channel length (x-axis). As shown in graph **222**, the leakage current of an NMOS transistor is larger (e.g., approximately 5 times larger) than that of PMOS transistor with a same channel length. The lower leakage current provides ESD circuit **200** with a low power consumption since the SiGe PMOS shunt transistor **218** consumes less power (i.e., current) when it is not in use.

Furthermore, in emerging technology nodes (e.g., 28 nm, 22 nm, etc.) a SiGe PMOS shunt transistor **218** has a PMOS drive strength that is comparable to NMOS drive strength. For example, FIG. 2C illustrates a graph **224** showing the saturation drive current (ID_{sat}) of both NMOS and PMOS shunt transistors (y-axis) as a function of channel length (x-axis).

As shown in graph **224**, the saturation drive current (ID_{sat}) is substantially equivalent for both NMOS and PMOS transistors with a same channel length. For example, a PMOS transistor with a normalized channel length of 2 has a saturation drive current that is within approximately 20% of that of an NMOS transistor with a same channel length. Therefore, the SiGe PMOS transistor provides ESD circuit **200** with a performance that is comparable to ESD circuits having an NMOS shunt transistor.

During operation, the PMOS shunt transistor **218** is configured to turn on and off based upon a value of the trigger signal S_{trig} (e.g., a voltage provided directly from the trigger circuit output node **212**). For example, in the absence of an ESD event **106** capacitive element **210** acts as an open, providing the second voltage to trigger circuit output node **212**. The second voltage is output as a trigger signal S_{trig} having a relatively high voltage (e.g., representing logical “1” state), which is provided to the gate of the PMOS shunt transistor **218**. The relatively high voltage turns off the PMOS shunt transistor **218**, preventing leakage between the first and second circuit nodes, **112** and **114**, during normal operation. If an ESD event **106** is present, trigger circuit **206** has a RC time constant delay defined by resistive element **208** and capacitive element **210**, during which the trigger circuit **206** provides a second voltage to trigger circuit output node **212**. The second voltage is output as a trigger signal S_{trig} having a relatively low voltage (e.g., representing logical “0” state) before the RC time constant is reached. The trigger signal S_{trig} is provided to the gate of the PMOS shunt transistor **218**, thereby turning on the PMOS shunt transistor **218** and causing energy to be diverted away from the ESD-susceptible circuit **104** via the second electrical path **214** (i.e., along path P_{ESD}).

In some embodiments, the ESD circuit **200** further comprises a timing delay circuit **220**. The timing delay circuit **220** is configured to extend the time that PMOS shunt transistor **218** is turned on while the ESD event **106** is present (i.e., to increase the turn-on-time to a time greater than the RC time constant of the trigger circuit **206**), without influencing operation of the PMOS shunt transistor **218** when the ESD event **106** is not present. By extending the turn-on-time of the PMOS shunt transistor **218** during the ESD event **106**, the ESD capabilities of the integrated circuit **200** are improved.

FIG. 3 illustrates a circuit schematic of some embodiments of a disclosed ESD protection device **300** having a SiGe PMOS shunt transistor **322**.

The ESD protection device **300** comprises an RC trigger circuit **304** having a resistive element **208** and a MOS capacitor **308** connected in series along a first path **306**. In some embodiments, the resistive element **208** comprises a polysilicon resistor, for example. In other embodiments, the resistive element **208** comprises a diffusion resistor. In some embodiments, the MOS capacitor **308** comprises a MOSFET transistor having a gate connected to trigger circuit output node **212**, a source connected to a drain and to a second circuit node **114**, and a body connected to a third circuit node **324** connected to a third external pin **326**. In some embodiments, the second and third circuit nodes, **114** and **324**, are held at a ground potential. By shorting the drain and source, the MOSFET transistor acts as a MOS capacitor **308** having a gate oxide that acts as an insulator of the capacitor. Also, by connecting the body of MOS capacitor **308** to a third circuit node **324** comprising a ground terminal the trigger circuit **304** can generate a trigger signal S_{trig1} having a low value when ESD event is present (e.g., a logical “0”).

The trigger circuit output node **212** is further connected to a timing delay circuit **310** comprising an inverter **312** config-

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ured to drive an NMOS transistor **318**. In some embodiments, the inverter **312** comprises a first, pull-up transistor **314** and a second, pull-down transistor **316**, connected in series between the first and second circuit nodes, **112** and **114**. In some embodiments, the pull-up transistor **314** comprises a PMOS transistor having a source connected to the first circuit node **112** and a gate connected to the trigger circuit output node **212**, and the pull-down transistor **316** comprises an NMOS transistor having a source connected to the second circuit node **114**, a drain connected to the drain of the pull-up transistor **314**, and a gate connected to the trigger circuit output node **212**. In some embodiments, the PMOS pull-up transistor **314** and the NMOS pull-down transistor **316** have source to body connections. The NMOS transistor **318** has a drain connected to the trigger circuit output node **212**, a source connected to the second circuit node **114**, and a gate connected to an output terminal of the inverter **312** (i.e., the drains of transistors **314** and **316**).

The timing delay circuit **310** is configured to extend the turn-on-time of a SiGe PMOS shunt transistor **322** while an ESD event **106** is present, and to not influence operation of the SiGe PMOS shunt transistor **322** when the ESD event **106** is not present. In some embodiments, the timing delay circuit **310** is configured to extend the turn-on-time of SiGe PMOS shunt transistor **322** by selectively connecting the trigger circuit output node **212** to the second circuit node **114** (e.g., GND) when the ESD event **106** is present. In such an embodiment, the introduced timing delay comprises the time that it takes to change the state of transistors **314-318** (i.e., the delay time of transistor **314** or **316** and transistor **318**).

For example, when an ESD event **106** is not present the trigger circuit output node **212** has a relatively high voltage value, which provides a trigger signal S_{trig} having a logical “1” to the gates of transistors **314** and **316**. The trigger signal S_{trig} having a logical “1” turns off the pull-up transistor **314** and turns on the pull-down transistor **316**, causing the inverter **312** to invert the trigger signal S_{trig} and to output a signal having a logical “0” to the gate of NMOS transistor **318**. The signal having a logical “0” turns off NMOS transistor **318**, causing the trigger signal that is provided to the gate of SiGe PMOS shunt transistor **322** to have a logical “1”. Therefore, when an ESD event **106** is not present the timing delay circuit **310** does not effect operation of the SiGe PMOS shunt transistor **322**.

However, when an ESD event **106** is present the trigger circuit output node **212** has a relatively low voltage value during the RC time constant, which provides a trigger signal S_{trig} having a logical “0” to the gates of transistors **314** and **316**. The trigger signal S_{trig} having a logical “0” turns on the pull-up transistor **314** and turns off the pull-down transistor **316**, causing the inverter **312** to invert the trigger signal S_{trig} and to output a signal having a logical “1” to the gate of NMOS transistor **318**. The signal having a logical “1” turns on NMOS transistor **318**, causing the trigger circuit output node **212** and the gate of the PMOS shunt transistor **322** to be held low until the trigger signal S_{trig} level is pulled up by ESD event **106**. Therefore, the timing delay circuit **310** will introduce a time delay, comprising the time that it takes to change the state of transistors **314** or **316** and transistor **318**, before PMOS shunt transistor **322** is turned off (i.e., before the gate voltage is a logical “1”). For example, during power on, the trigger signal S_{trig} has a logical “0” causing ESD current to flow through resistor **208**, NMOS transistor **308**, and NMOS transistor **318**. The current flowing through NMOS transistor **318** will change the value of the trigger signal S_{trig} , which will

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slowly turn off PMOS transistor **314** and turn on NMOS transistor **316**, so that NMOS transistor **318** will slowly be turned off

In some embodiments, a second electrical path **324** comprises a voltage controlled shunt network **320** having a SiGe PMOS shunt transistor **322** that comprises a body connected device. The body connected, SiGe PMOS shunt transistor **322** has a body that is connected to a source of the PMOS shunt transistor **322**. The source to body connection varies the bias voltage that is applied to the body, changing the threshold voltage of the PMOS shunt transistor **322** via the body effect. For the SiGe PMOS shunt transistor **322**, biasing the body with a positive voltage reduces the magnitude of the threshold voltage needed to turn on the transistor.

FIG. 4 illustrates some alternative embodiments of an integrated circuit **400** having a disclosed ESD protection device **402** configured to protect an ESD susceptible circuit **104**.

The ESD protection device **402** comprises a first electrical path **404** comprising a trigger circuit **406**. The trigger circuit **406** comprises a resistive element **408** having a first terminal connected to a first circuit node **112** and a second terminal connected to a trigger circuit output node **410**. The trigger circuit output node **410** is further connected to the gate of SiGe PMOS shunt transistor **218**, so that the resistive element **408** is disposed between the first circuit node **112** and the gate of the SiGe PMOS shunt transistor **218**. Since the resistive element **408** is connected directly to the gate of the SiGe PMOS shunt transistor **218**, the SiGe PMOS shunt transistor **218** operates as a capacitive element of the trigger circuit **406**. Since the capacitive element of trigger circuit **406** comprises SiGe PMOS shunt transistor **218**, SiGe PMOS shunt transistor **218** is selected to have a gate capacitance with a capacitive value that provides for an RC time constant that is sufficiently large to generate a trigger signal that activates the PMOS shunt transistor **218** for a period of time that is larger than the duration of the ESD event **106**.

A voltage controlled shunt network **216** is electrically connected to a second electrical path **214** that extends between the first and second circuit nodes, **112** and **114**. The second electrical path **214** comprises the SiGe PMOS shunt transistor **218**. Therefore, the first and second electrical paths, **404** and **214**, share the SiGe PMOS shunt transistor **218**, such that the second electrical path **214** coincides with a section of the first electrical path **404**.

In the absence of an ESD event **106**, the gate capacitance of the PMOS shunt transistor **218** causes a relatively high voltage (e.g., representing logical “1” state) to be provided from the first circuit node **112** to the gate of SiGe PMOS shunt transistor **218**. The relatively high voltage turns off SiGe PMOS shunt transistor **218**, causing energy to flow to from the external pins **108**, **110** to the ESD susceptible circuit **104**. If an ESD event **106** is present, the gate capacitance of SiGe PMOS shunt transistor **218** causes a relatively low voltage (e.g., representing a logical “0” state) to be provided to the gate of SiGe PMOS shunt transistor **218**, thereby turning on SiGe PMOS shunt transistor **218** and causing energy to flow over the second electrical path **214** such that the energy of the ESD event **106** is diverted away from the ESD-susceptible circuit **104**.

Accordingly, by utilizing the gate capacitance of SiGe PMOS shunt transistor **218** as the capacitive element of trigger circuit **406**, the trigger circuit **406** can achieve a sufficient RC time constant without having a capacitive element specifically designated to operate as part of the RC trigger circuit. In other words, the layout area of the ESD protection device

402 is reduced by using SiGe PMOS shunt transistor **218** as both a shunt transistor and a capacitive element of the trigger circuit **406**.

FIG. 5 illustrates a circuit schematic of some alternative embodiments of a disclosed ESD protection device **500** having a SiGe PMOS shunt transistor **322**.

The ESD protection device **500** comprises a first electrical path **404** comprising a trigger circuit **406** having a resistive element **408** connected to a trigger circuit output node **410**. The trigger circuit output node **410** is connected to a timing delay circuit **310** comprising an inverter **312** configured to drive operation of an NMOS transistor **318**. The timing delay circuit **310** is configured to extend the turn-on-time of SiGe PMOS shunt transistor **322** while ESD event **106** is present, and to not influence operation of SiGe PMOS shunt transistor **322** when ESD event **106** is not present.

The ESD protection device **500** further comprises a diode **504** connected between the first and second circuit nodes, **112** and **114**. The diode **504** is configured to allow current to pass from the second circuit node **114** to the first circuit node **112**. The diode **504** provides a discharge path for current generated by a negative ESD event.

FIG. 6 shows some embodiments of a cross-sectional view of a substrate **600** comprising a silicon germanium (SiGe) PMOS shunt transistor **602** and a resistive element **626**.

The SiGe PMOS shunt transistor **602** comprises first and second p-type silicon germanium (SiGe) regions **608a**, **608b** within an n-type substrate. In some embodiments, the n-type substrate comprises an n-type epitaxial layer **606** disposed onto a semiconductor body **604** comprising a bulk silicon substrate. In some embodiments, the SiGe PMOS shunt transistor **602** comprises p-type drain extension regions **610a**, **610b** located within the epitaxial layer **606** at a position adjacent to the p-type SiGe regions **608a**, **608b**.

The p-type SiGe regions **608a** and **608b** operate as source and drain regions within SiGe PMOS shunt transistor **602**. A source electrode S is electrically connected to the first p-type SiGe region **608a** and a drain electrode D is electrically connected to the second p-type SiGe region **608b**. A channel region **612** extends between the first and second p-type SiGe regions, **608a** and **608b**. In some embodiments, the channel region **612** may comprise strained silicon having an n-type doping.

A gate electrode **616** is located over the channel region **612**. The gate electrode **616** is separated from the channel region **612** by a gate oxide **614**. During operation, when a relatively large voltage (e.g., a logical “1”) is applied to the gate electrode **616**, it turns off the SiGe PMOS shunt transistor **602** so that substantially no current flows in the channel region **612** between the source electrode S and the drain electrode D. When a relatively small voltage (e.g., a logical “0”) is applied to the gate electrode **616**, it turns on the SiGe PMOS shunt transistor **602** so that current flows in the channel region **612** between the source electrode S and the drain electrode D.

The gate electrode **616** is connected to a contact **618** disposed within a dielectric material **622**. The contact **618** electrically connects the gate electrode **616** to a first metal interconnect layer **624**. The first metal interconnect layer **624** is further connected to resistive element **626**. As shown, the resistive element **626** comprises a polysilicon resistor, which is positioned between an external pin (not shown) and the gate electrode **616** of the SiGe PMOS shunt transistor **602**. In some embodiments, the resistive element **626** comprises a polysilicon material **630**, having a length proportional to the resistance of the resistive element **626**, which is connected to the first metal interconnect layer **624** by way of a contact **620** and a silicide layer **628**. In other embodiments, the resistive

element **626** may comprise an oxide definition resistor (e.g., a resistor comprising an active area within the semiconductor substrate, which is implanted to have a doping concentration that provides for a specific resistance).

FIG. 7 illustrates a flow diagram of some embodiments of a method **700** of forming an ESD protection device having a SiGe PMOS shunt transistor. While method **700** is illustrated and described below as a series of acts or events, it will be appreciated that the illustrated ordering of such acts or events are not to be interpreted in a limiting sense. For example, some acts may occur in different orders and/or concurrently with other acts or events apart from those illustrated and/or described herein. In addition, not all illustrated acts may be required to implement one or more aspects or embodiments of the description herein. Further, one or more of the acts depicted herein may be carried out in one or more separate acts and/or phases.

At step **702**, an ESD susceptible circuit that is electrically connected to a first circuit node having a first voltage and a second circuit node having a second voltage is provided. In some embodiments, the first voltage comprises a source voltage (e.g., 3.3V) and the second voltage comprises a ground voltage (e.g., 0V).

At step **704**, a trigger circuit is provided. The trigger circuit comprises a resistive element connected with a capacitive element at a trigger circuit output node. The resistive element has a first terminal connected to the first circuit node and a second terminal connected to a trigger circuit output node. In some embodiments, the capacitive element comprises the gate capacitance of a shunt transistor extending between the first circuit node and the second circuit node.

At step **706**, a SiGe PMOS shunt transistor having a gate directly connected to the trigger circuit output node (i.e., the second terminal of the resistive element) is provided. By directly connecting the trigger circuit output node to the gate of the SiGe PMOS shunt transistor, the gate of the SiGe PMOS shunt transistor receives a voltage value that is substantially equal to the voltage value at the trigger circuit output node (i.e., that corresponds to a same logical state).

In some embodiments, the trigger circuit output node is connected to a timing delay circuit configured to extend turn on time of the SiGe PMOS shunt transistor, at step **708**. In some embodiments, the timing delay circuit comprises an inverter configured to receive the voltage at the trigger circuit output node and a NMOS transistor configured to selectively connect the gate of the PMOS shunt transistor to a ground terminal based upon the output of the inverter. By selectively connecting the gate of the PMOS shunt transistor to a ground terminal based upon the output of the inverter, the turn-on-time of the SiGe PMOS shunt transistor is extended. This is because when an ESD event passes, the voltage at the trigger circuit output node will remain low for a delay time equal to the time that it takes for the inverter to turn off the NMOS transistor and therefore to disconnect the trigger circuit output node from the second circuit node (e.g., GND).

It will be appreciated that identifiers such as “first” and “second” do not imply any type of ordering or placement with respect to other elements; but rather “first” and “second” and other similar identifiers are just generic identifiers. In addition, it will be appreciated that the term “electrically connected” includes direct and indirect connections. For example, if element “a” is electrically connected to element “b”, element “a” can be electrically connected directly to element “b” and/or element “a” can be electrically connected to element “b” through element “c”, so long as there is an operable electrical connection between elements “a” and “b”.

While the disclosure has been illustrated and described with respect to one or more implementations, alterations and/or modifications may be made to the illustrated examples without departing from the spirit and scope of the appended claims. In particular regard to the various functions performed by the above described components or structures (assemblies, devices, circuits, systems, etc.), the terms (including a reference to a “means”) used to describe such components are intended to correspond, unless otherwise indicated, to any component or structure which performs the specified function of the described component (e.g., that is functionally equivalent), even though not structurally equivalent to the disclosed structure which performs the function in the herein illustrated exemplary implementations of the disclosure. In addition, while a particular feature of the disclosure may have been disclosed with respect to only one of several implementations, such feature may be combined with one or more other features of the other implementations as may be desired and advantageous for any given or particular application. Furthermore, to the extent that the terms “including”, “includes”, “having”, “has”, “with”, or variants thereof are used in either the detailed description and the claims, such terms are intended to be inclusive in a manner similar to the term “comprising”.

Therefore, the present disclosure relates to an area efficient ESD circuit comprising a SiGe PMOS shunt transistor that is configured to provide for a low leakage current.

In some embodiments, the present disclosure relates to an integrated chip, comprising an electrostatic discharge (ESD) susceptible circuit electrically connected to a first circuit node having a first voltage and a second circuit node having a second voltage. An ESD protection device, configured to act as an interface between the ESD susceptible circuit and external integrated chip pins, comprises a trigger circuit configured to generate a trigger signal, having a value dependent upon an ESD event, at a trigger circuit output node. The ESD protection device further comprises a voltage controlled shunt network comprising a silicon germanium (SiGe) PMOS shunt transistor with a source connected to the first circuit node, a drain connected to the second circuit node, and a gate connected directly to the trigger circuit output node and configured to receive a voltage value that is substantially equal to a voltage value of the trigger signal.

In other embodiments, the present disclosure relates to an electrostatic discharge (ESD) protection device to protect a circuit, which is electrically connected to first and second circuit nodes, from an ESD event. The ESD protection device comprises a first electrical path extending between first and second circuit nodes and having a trigger circuit comprising a resistive element and a capacitive element connected to one another at a trigger circuit output node. The ESD protection device further comprises a second electrical path extending between the first and second circuit nodes and comprising a silicon germanium (SiGe) PMOS shunt transistor with a source connected to the first circuit node, a drain connected to the second circuit node, and a gate connected directly to the trigger circuit output node.

In other embodiments, the present disclosure relates to method of forming an ESD protection device. The method comprises, providing an electrostatic discharge (ESD) susceptible circuit electrically connected to a first circuit node having a first voltage and a second circuit node having a second voltage. The method further comprises, providing a trigger circuit comprising a resistive element having a first terminal connected to the first circuit node and a second terminal connected to a trigger circuit output node. The method further comprises, directly connecting a gate of a

SiGe PMOS shunt transistor to the trigger circuit output node so that the gate of the SiGe PMOS shunt transistor receives a voltage value that is substantially equal to a voltage value at the trigger circuit output node.

What is claimed is:

1. An integrated chip, comprising:

an electrostatic discharge (ESD) susceptible circuit electrically connected to a first circuit node having a first voltage and a second circuit node having a second voltage; and

an ESD protection device, configured to act as an interface between the ESD susceptible circuit and external integrated chip pins, comprising:

a trigger circuit comprising a resistive element having a first terminal connected to the first circuit node and a second terminal directly connected to a trigger circuit output node, and a capacitive element having a first terminal directly connected to the trigger circuit output node and a second terminal connected to the second circuit node; and

a voltage controlled shunt network comprising a silicon germanium (SiGe) PMOS shunt transistor with a source connected to the first circuit node, a drain connected to the second circuit node, and a gate connected directly to the trigger circuit output node.

2. The integrated chip of claim 1, wherein the capacitive element comprises a gate capacitance of the SiGe PMOS shunt transistor.

3. The integrated chip of claim 1, wherein the capacitive element comprises a MOS capacitor having a source and drain connected to the drain of the SiGe PMOS shunt transistor, a gate connected to the resistive element, and a body connected to a third circuit node comprising a ground terminal.

4. The integrated chip of claim 1, further comprising:

a timing delay circuit having an input node connected to the trigger circuit output node, wherein the timing delay circuit is configured to selectively connect the trigger circuit output node to a ground terminal when an ESD event is present so as to extend a turn-on-time of the SiGe PMOS shunt transistor.

5. The integrated chip of claim 4, wherein the timing delay circuit comprises:

an inverter having a first inverting element and a second inverting element arranged in series between the first circuit node and the second circuit node, wherein an input node of the inverter is connected to the trigger circuit output node; and

an NMOS transistor having a gate connected to an output terminal of the inverter, a drain connected to the trigger circuit output node, and a source connected to the second circuit node.

6. The integrated chip of claim 5, wherein the first inverting element comprises a PMOS transistor having a source to body connection; and the second inverting element comprises an NMOS transistor having a source to body connection.

7. The integrated chip of claim 1, wherein the SiGe PMOS shunt transistor comprises:

a source region comprising a first, p-type SiGe region within an n-type substrate;

a drain region comprising a second, p-type SiGe region within the n-type substrate;

a channel region extending between the first and second p-type SiGe regions;

a gate electrode located over the channel region, and separated from the channel region by a gate oxide; and

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a first metal interconnect layer configured to connect the gate electrode to a polysilicon resistor or an oxide definition resistor that comprises the resistive element.

8. The integrated chip of claim 1, wherein the SiGe PMOS shunt transistor comprises a source to body connection.

9. The ESD protection device of claim 1, wherein the first terminal of the capacitive element is the gate of the SiGe PMOS shunt transistor.

10. The ESD protection device of claim 1, wherein the trigger circuit consists of the trigger circuit output node, the resistive element, and the capacitive element.

11. An electrostatic discharge (ESD) protection device to protect a circuit, which is electrically connected to first and second circuit nodes, from an ESD event, the ESD protection device comprising:

a first electrical path extending between first and second circuit nodes and having a trigger circuit comprising a resistive element and a capacitive element connected to one another at a trigger circuit output node;

a second electrical path extending between the first and second circuit nodes and comprising a silicon germanium (SiGe) PMOS shunt transistor with a source connected to the first circuit node, a drain connected to the second circuit node, and a gate connected directly to the trigger circuit output node; and

a timing delay circuit having an input node connected to the trigger circuit output node, wherein the timing delay circuit is configured to selectively connect the trigger circuit output node to a ground terminal when the ESD event is present so as to extend a turn-on-time of the SiGe PMOS shunt transistor.

12. The ESD protection device of claim 11, wherein the capacitive element comprises a gate capacitance of the SiGe PMOS shunt transistor, such that a section of the first electrical path is coincident with a section of the second electrical path.

13. The ESD protection device of claim 11, wherein the first electrical path is in parallel with the second electrical path; and

wherein the capacitive element comprises a MOS capacitor having a source and drain connected to the drain of the SiGe PMOS shunt transistor, a gate connected to the resistive element, and a body connected to a third circuit node comprising a ground terminal.

14. The ESD protection device of claim 11, wherein the timing delay circuit comprises:

an inverter having a first inverting element and a second inverting element arranged in series between the first circuit node and the second circuit node, wherein the inverter is configured to receive a trigger signal from the trigger circuit; and

an NMOS transistor having a gate connected to an output terminal of the inverter, a drain connected to the trigger circuit output node, and a source connected to the second circuit node.

15. The ESD protection device of claim 11, wherein the SiGe PMOS shunt transistor comprises:

a source region comprising a first, p-type SiGe region within an n-type substrate;

a drain region comprising a second, p-type SiGe region within the n-type substrate;

a channel region extending between the first and second p-type SiGe regions;

a gate electrode located over the channel region, and separated from the channel region by a gate oxide; and

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a first metal interconnect layer configured to connect the gate electrode to a polysilicon resistor comprising the resistive element.

16. A method of forming an ESD protection device, comprising:

providing an electrostatic discharge (ESD) susceptible circuit electrically connected to a first circuit node having a first voltage and a second circuit node having a second voltage;

providing a trigger circuit comprising:

a resistive element having a first terminal connected to the first circuit node and a second terminal directly connected to a trigger circuit output node;

a capacitive element having a first terminal directly connected to the trigger circuit output node and a second terminal connected to the second circuit node; and

directly connecting a gate of a SiGe PMOS shunt transistor to the trigger circuit output node so that the gate of the SiGe PMOS shunt transistor receives a voltage value that is substantially equal to a voltage value at the trigger circuit output node.

17. The method of claim 16, wherein the SiGe PMOS shunt transistor comprises a source to body connection.

18. The method of claim 16, wherein the capacitive element comprises a gate capacitance of the SiGe PMOS shunt transistor.

19. The method of claim 16, further comprising:

selectively connecting the trigger circuit output node to a ground terminal when an ESD event is present so as to extend a turn-on-time of the SiGe PMOS shunt transistor.

wherein the first terminal of the capacitive element is the gate of the SiGe PMOS shunt transistor.

20. An electrostatic discharge (ESD) protection device to protect a circuit, which is electrically connected to first and second circuit nodes, from an ESD event, the ESD protection device comprising:

a first electrical path extending between first and second circuit nodes and having a trigger circuit comprising a resistive element and a capacitive element connected to one another at a trigger circuit output node;

a second electrical path extending between the first and second circuit nodes and comprising a PMOS shunt transistor with a source connected to the first circuit node, a drain connected to the second circuit node, and a gate connected to the trigger circuit output node; and

a timing delay circuit having an input node connected to the trigger circuit output node, wherein the timing delay circuit is configured to selectively connect the trigger circuit output node to a ground terminal when the ESD event is present so as to extend a turn-on-time of the PMOS shunt transistor.

21. The ESD protection device of claim 20, wherein the timing delay circuit comprises:

a pull-up transistor having a source connected to the first circuit node and a gate connected to the trigger circuit output node;

a pull-down transistor having a source connected to the second circuit node, a drain connected to a drain of the pull-up transistor, and a gate connected to the trigger circuit output node; and

a transistor having a gate connected to the drain of the pull-up transistor and the drain of the pull-down transistor, a drain connected to the trigger circuit output node, and a source connected to the second circuit node.